

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

4 2812

In re Patent Application of  
YAMAGATA et al.

Serial No. 09/993,890

Filed: November 27, 2001

For: Method For Manufacturing Nonvolatile Semiconductor  
Memory With Narrow Variation In Threshold Voltages of  
Memory Cells



Atty. Ref.: 925-219

Group: 2812

Examiner: unknown

\* \* \* \* \*

Assistant Commissioner for Patents  
Washington, DC 20231

Sir:

**INFORMATION DISCLOSURE STATEMENT**

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO-1449, a copy of each of which is enclosed.

Official citation and consideration of all the attached documents is requested. Please return to the undersigned a copy of the attached PTO-1449 with the examiner's initials in the left column [MPEP §609] with the next communication.

The filing of an Information Disclosure Statement shall not be construed as a representation that a search has been made [37 C.F.R. § 1.97(g)], an admission that the information cited is, or is considered to be, material to patentability or that no other material information exists. Further, the filing of an Information Disclosure Statement shall not be construed as an admission against interest in any manner [Commissioner's Notice of January 9, 1992, 1135 O.G. 12-25 at 25].

Respectfully submitted,  
NIXON & VANDERHYE P.C.

December 10, 2001

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